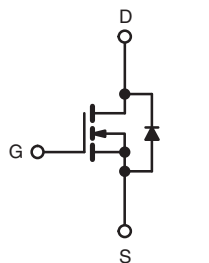
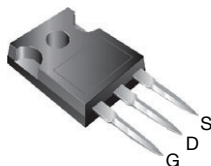


Power MOSFET

TO-247AC


N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	400	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.30
Q_g (Max.) (nC)	76	
Q_{gs} (nC)	20	
Q_{gd} (nC)	37	
Configuration	Single	

FEATURES

- Ultra low gate charge
- Reduced gate drive requirement
- Enhanced 30 V_{GS} rating
- Reduced C_{iss} , C_{oss} , C_{rss}
- Isolated central mounting hole
- Dynamic dV/dt rated
- Repetitive avalanche rated
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

This new series of low charge Power MOSFETs achieve significantly lower gate charge over conventional MOSFETs. Utilizing advanced MOSFETs technology the device improvements allow for reduced gate drive requirements, faster switching speeds and increased total system savings. These device improvements combined with the proven ruggedness and reliability of MOSFETs offer the designer a new standard in power transistors for switching applications.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole.

ORDERING INFORMATION

Package	TO-247AC
Lead (Pb)-free	IRFP350LCPbF

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	400	V
Gate-source voltage	V_{GS}	± 30	
Continuous drain current	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	A
		$T_C = 100\text{ }^{\circ}\text{C}$	
Pulsed drain Current ^a	I_{DM}	64	
Linear derating factor		1.5	W/ $^{\circ}\text{C}$
Single pulse avalanche energy ^b	E_{AS}	390	mJ
Repetitive avalanche current ^a	I_{AR}	16	A
Repetitive avalanche energy ^a	E_{AR}	19	mJ
Maximum power dissipation	P_D	190	W
Peak diode recovery dV/dt ^c	dV/dt	4.0	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Soldering recommendations (peak temperature) ^d	for 10 s	300 ^d	
Mounting torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 25\text{ V}$, starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 2.7\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 16\text{ A}$ (see fig. 12)
- $I_{SD} \leq 16\text{ A}$, $dI/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$
- 1.6 mm from case

**THERMAL RESISTANCE RATINGS**

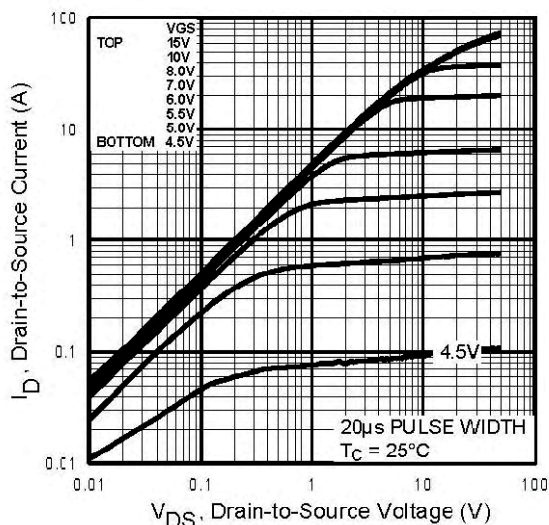
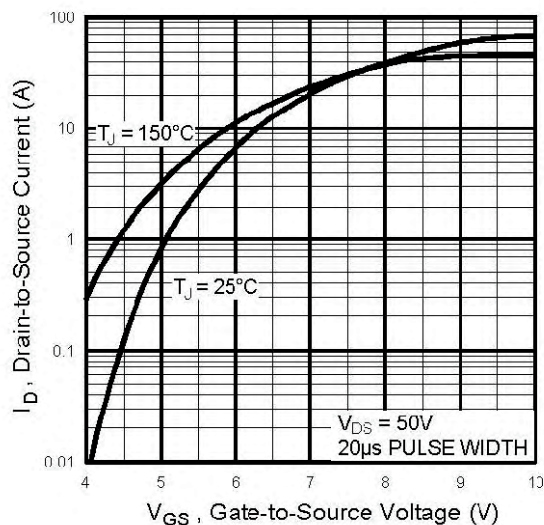
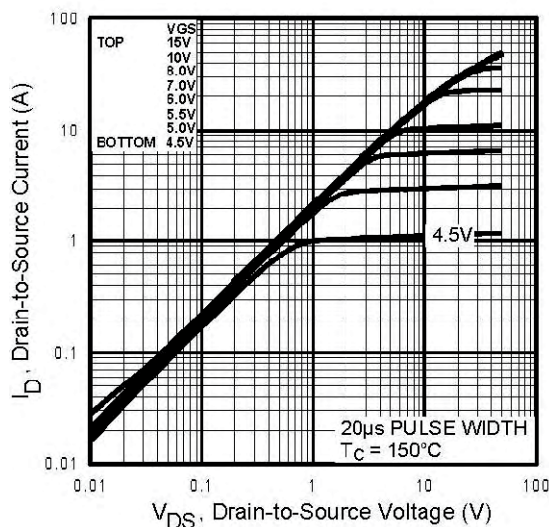
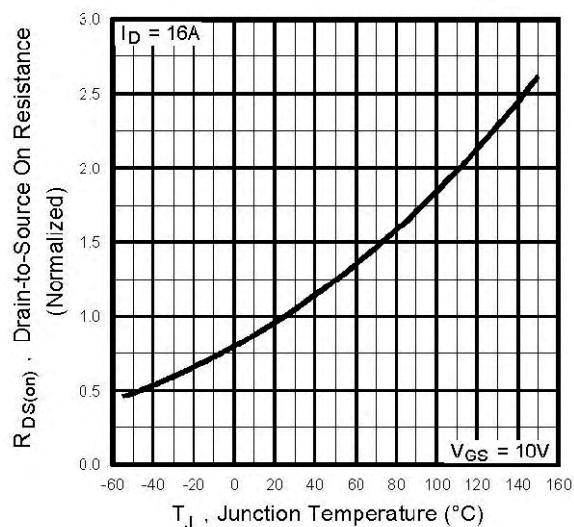
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.24	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.65	

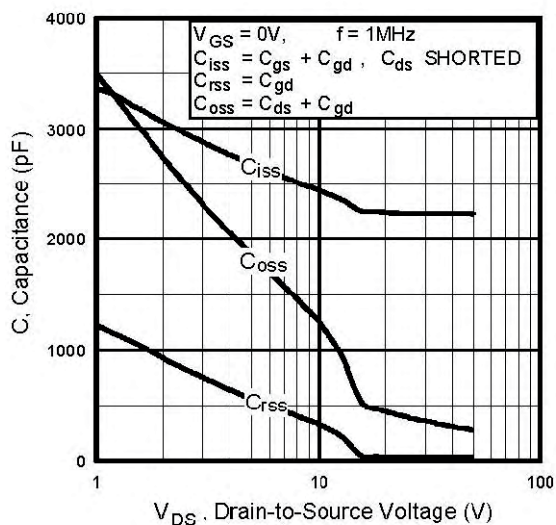
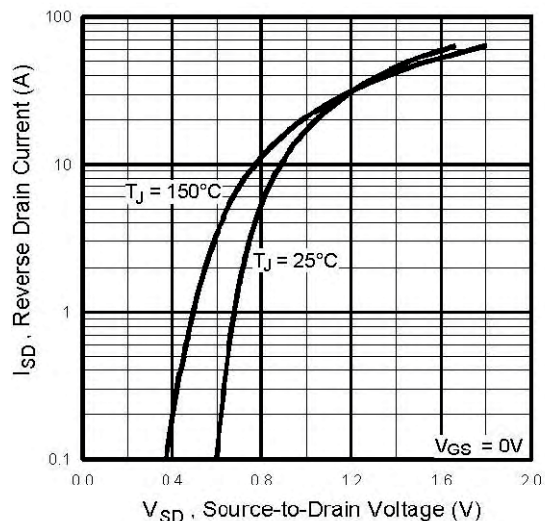
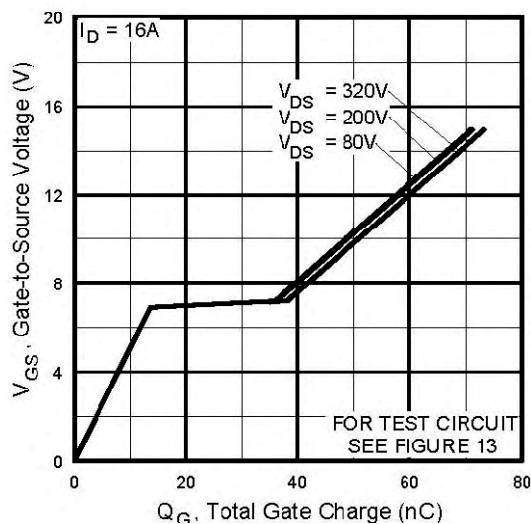
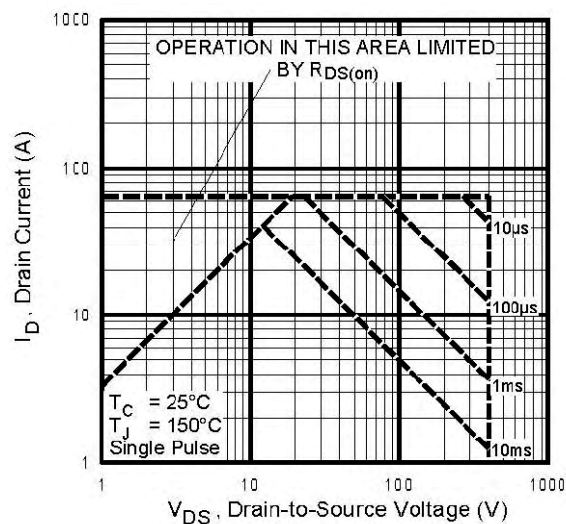
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

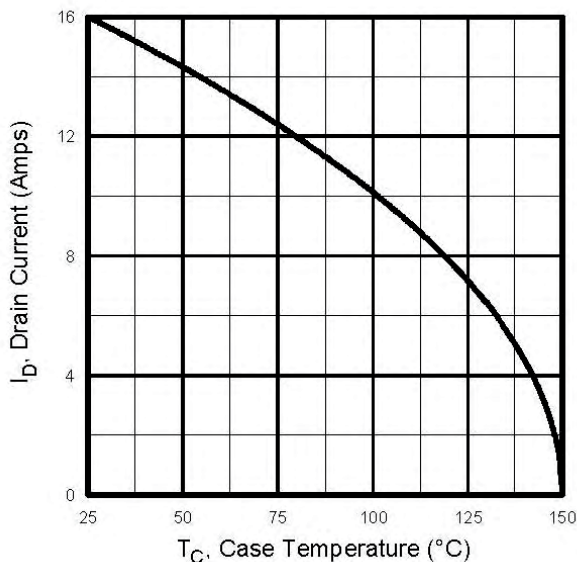
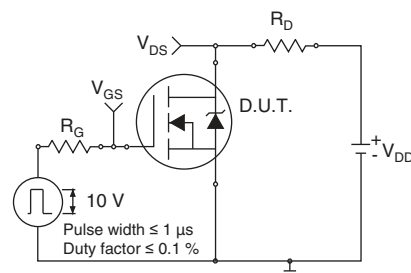
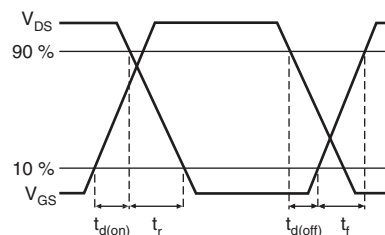
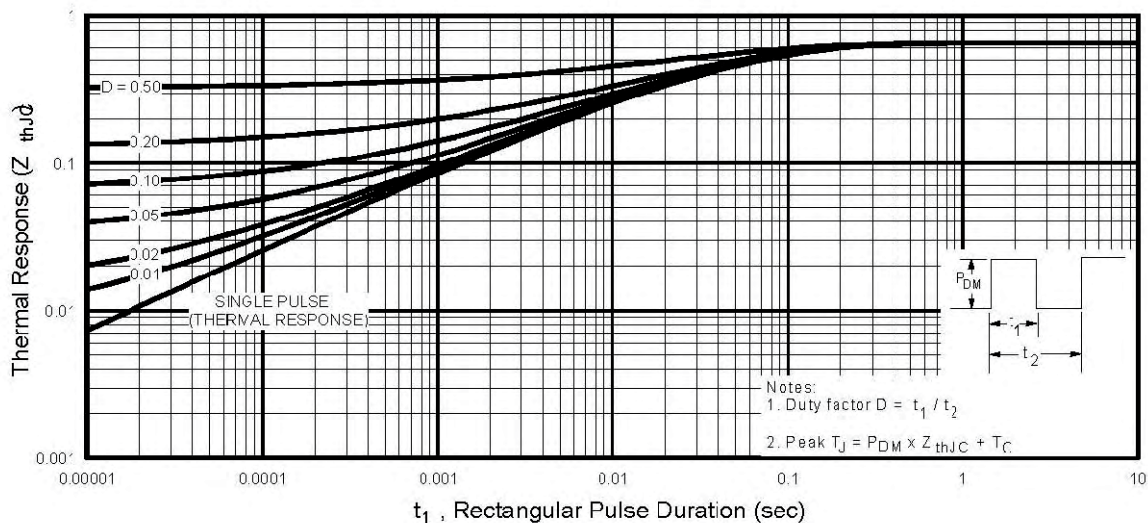
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$		400	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.49	-	V/ $^\circ\text{C}$
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 320\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 9.6\text{ A}^b$	-	-	0.30	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 9.6\text{ A}^b$		8.1	-	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5		-	2200	-	pF
Output capacitance	C_{oss}			-	390	-	
Reverse transfer capacitance	C_{rss}			-	31	-	
Total Gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 16\text{ A}$, $V_{DS} = 320\text{ V}$ see fig. 6 and 13 ^b	-	-	76	nC
Gate-source charge	Q_{gs}			-	-	20	
Gate-drain charge	Q_{gd}			-	-	37	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 200\text{ V}$, $I_D = 16\text{ A}$, $R_g = 6.2\text{ }\Omega$, $R_D = 12\text{ }\Omega$, see fig. 10 ^b		-	14	-	ns
Rise time	t_r			-	54	-	
Turn-off delay time	$t_{d(off)}$			-	33	-	
Fall time	t_f			-	35	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	16	A
Pulsed diode forward current ^a	I_{SM}			-	-	64	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 16\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 16\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$		-	440	660	ns
Body diode reverse recovery charge	Q_{rr}			-	4.1	6.2	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

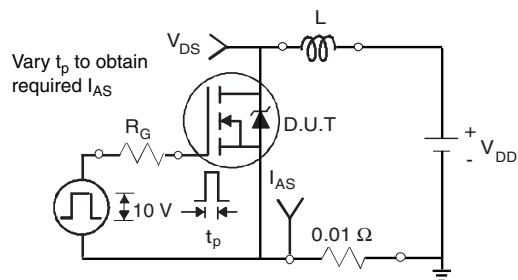
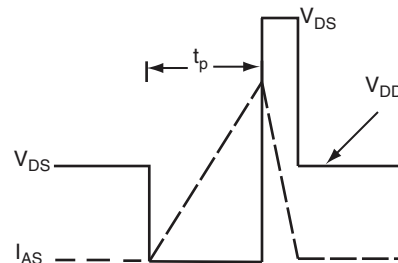
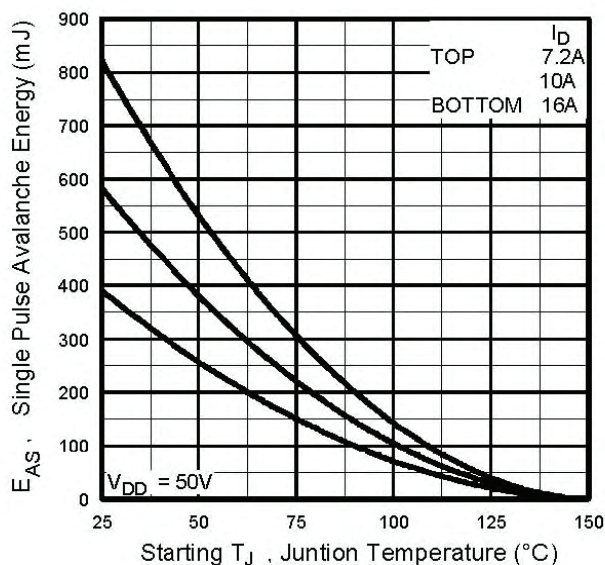
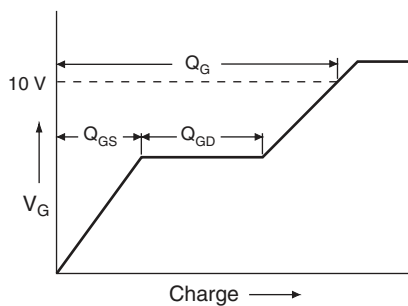
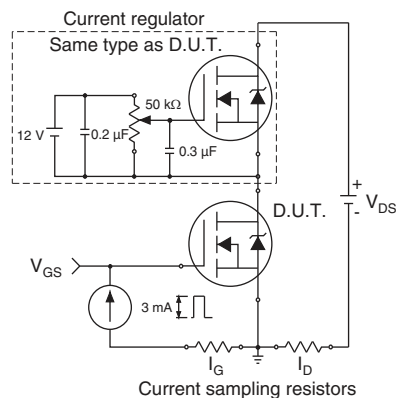
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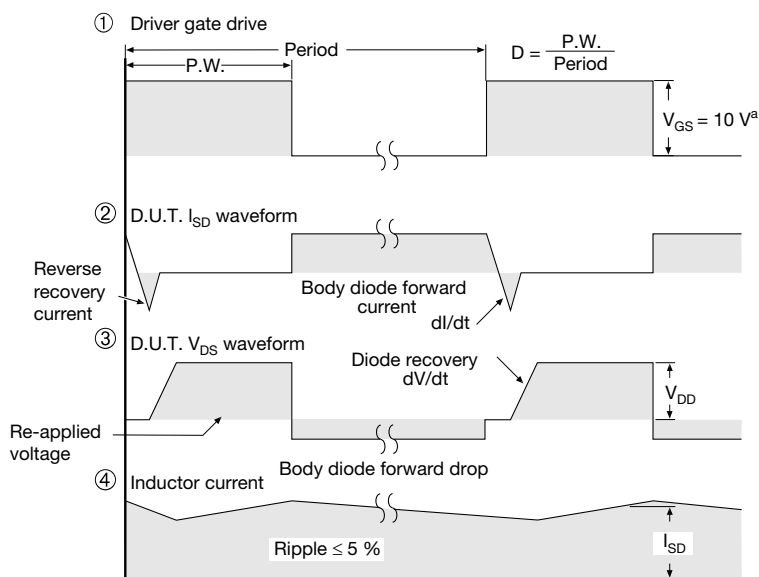
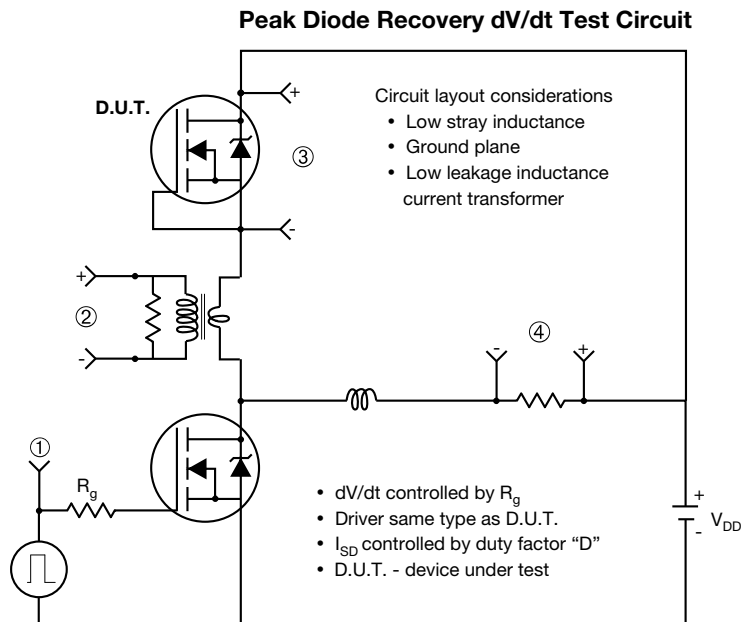
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10 - Switching Time Test Circuit

Fig. 11 - Switching Time Waveforms

Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 13 - Unclamped Inductive Test Circuit

Fig. 14 - Unclamped Inductive Waveforms

Fig. 15 - Maximum Avalanche Energy vs. Drain Current

Fig. 16 - Basic Gate Charge Waveform

Fig. 17 - Gate Charge Test Circuit


Note

a. $V_{GS} = 5 V$ for logic level devices

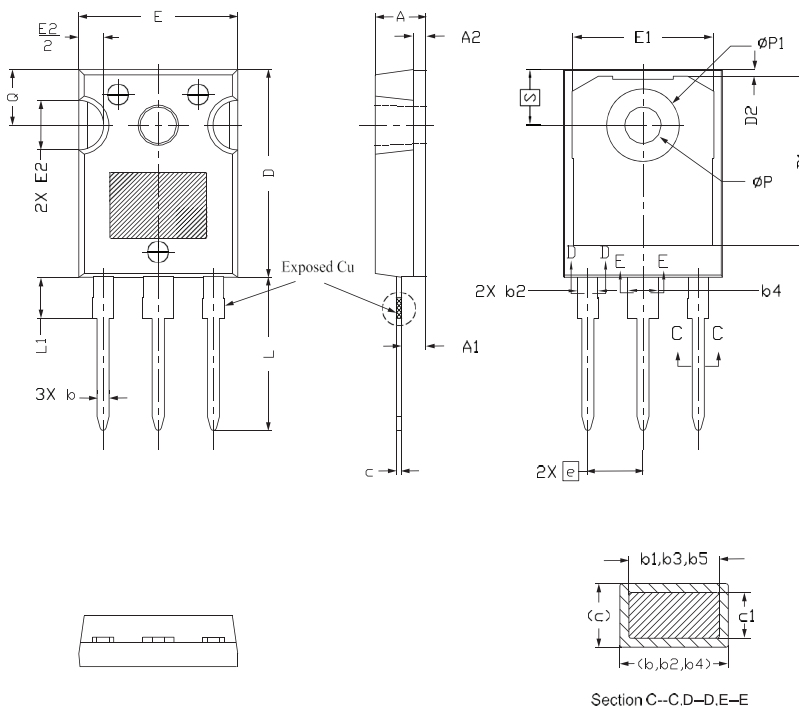
Fig. 18 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9



Section C--C,D--D,E--E

MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

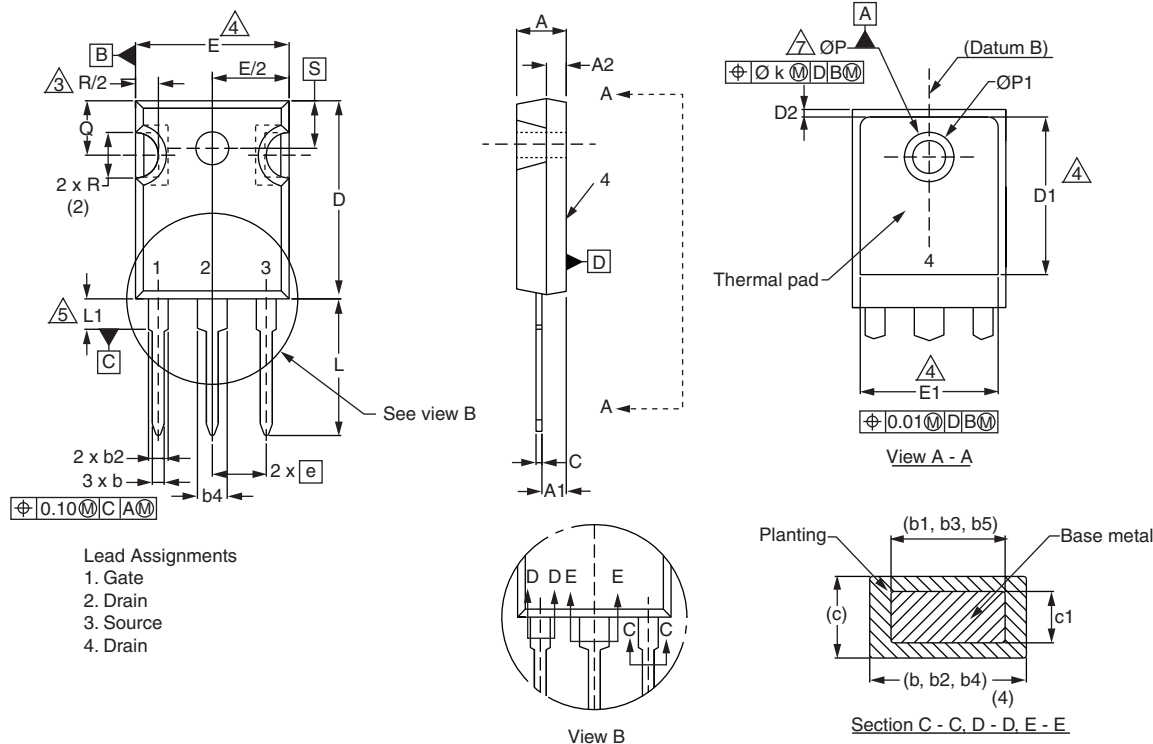
MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
e	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
Ø P	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S	5.51 BSC			

Notes

- Package reference: JEDEC® TO247, variation AC
- All dimensions are in mm
- Slot required, notch may be rounded
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions D1 and E1
- Lead finish uncontrolled in L1
- Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



VERSION 2: FACILITY CODE = Y



DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

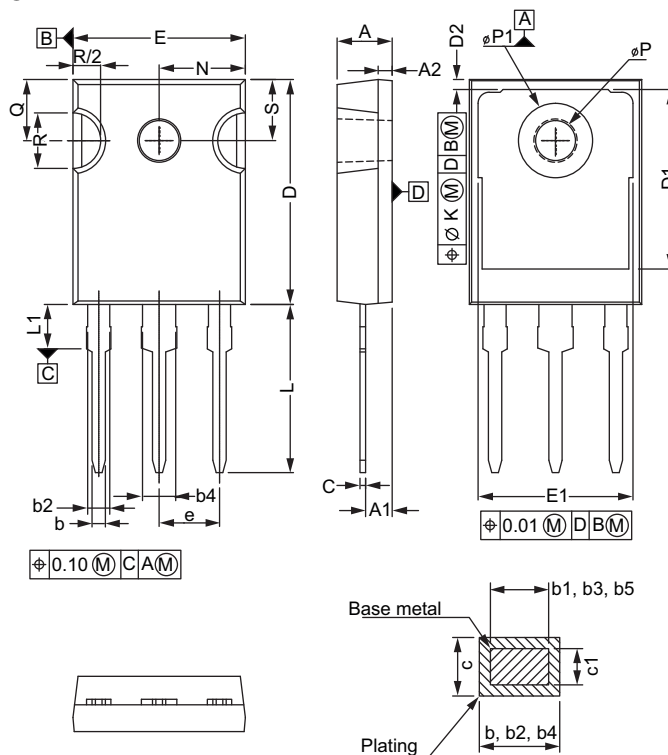
DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Contour of slot optional
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions D1 and E1
- Lead finish uncontrolled in L1
- Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

MILLIMETERS		
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

ECN: E22-0452-Rev. G, 31-Oct-2022
DWG: 5971

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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